

AMENDMENTS TO THE ABSTRACT:

Please replace the Abstract with the following:

A method for manufacturing a group III nitride compound semiconductor device includes irradiating a surface of a wafer with ultraviolet rays to thereby clean a resist residue from the surface of the wafer, the surface including a group III nitride compound semiconductor. The ultraviolet rays cause a reaction of oxygen molecules to form stimulated oxygen atoms having a strong oxidative power at the surface.